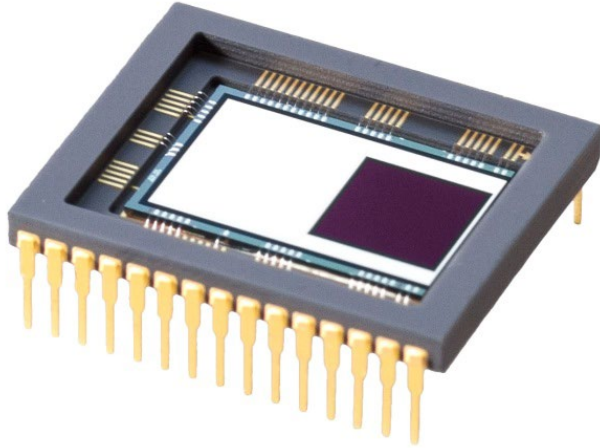


CCD97-00

512 x 512 BSI EMCCD



KEY FEATURES

- 512 x 512 active pixels
- 16µm square pixels
- Single photon sensitive
- Variable multiplicative gain
- Additional conventional output amplifier
- Frame Transfer
- Inverted mode operation for low dark current
- 30-pin ceramic dual-in-line package

TYPICAL APPLICATIONS

- Advanced Microscopy
- Fast Astronomy
- Quantum Imaging

PART REFERENCES

Please see last page for full list of available parts.

GENERAL DATA

| Format | |
|--------------------------------|---|
| Image Area | 8.19 mm x 8.19 mm |
| Active Pixels | 512 x 512 (note 1) |
| Pixel Size | 16 µm x 16 µm |
| Number of output amplifiers | 2 (Electron multiplying and Conventional) |
| Package | |
| Package Size | 22.86 x 28.00 mm |
| Number of pins | 30 |
| Window | Removable Glass |
| Performance | |
| Typical Amplifier Responsivity | 5.3 µV/e ⁻ (OSH) 1.1 µV/e ⁻ (OSL) |
| Typical Readout Noise | <1e ⁻ at 1MHz at 1000x Gain 3.1e ⁻ at 50kHz using OSH amp. |
| Max Output data rate | 15MHz |
| Typical pixel charge capacity | 130 ke ⁻ /pixel |
| Typical dark signal (20°C) | 400 e ⁻ /pixel/s |

OVERVIEW

The CCD97 is a frame transfer, electron multiplying CCD sensor designed for extreme performance in high frame rate ultra-low light applications. The Teledyne e2v back-thinning process ensures high quantum efficiency over a wide range of wavelengths.

An electron multiplying CCD functions by having an extended readout register with variable gain from 1x to 1000x prior to voltage conversion in the output amplifier. This allows readout noise to be effectively eliminated while maintaining fast readout rates.

The device can also be read out without using the gain register via the High Responsivity Output amplifier (OSH) for high dynamic range.

The gain may be varied from 1x to over 1000x by adjustment of the multiplication phase amplitude $R\theta 2HV$

Whilst Teledyne e2v has taken care to ensure the accuracy of the information contained herein it accepts no responsibility for the consequences of any use thereof and also reserves the right to change the specification of goods without notice. Teledyne e2v accepts no liability beyond that set out in its standard conditions of sale in respect of infringement of third party patents arising from the use of tubes or other devices in accordance with information contained herein.

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Template: 1B300000-DFP Ver 1

A1A-CCD97BI-2P-IMO Version 10, May 2025

CM 5004996

PERFORMANCE

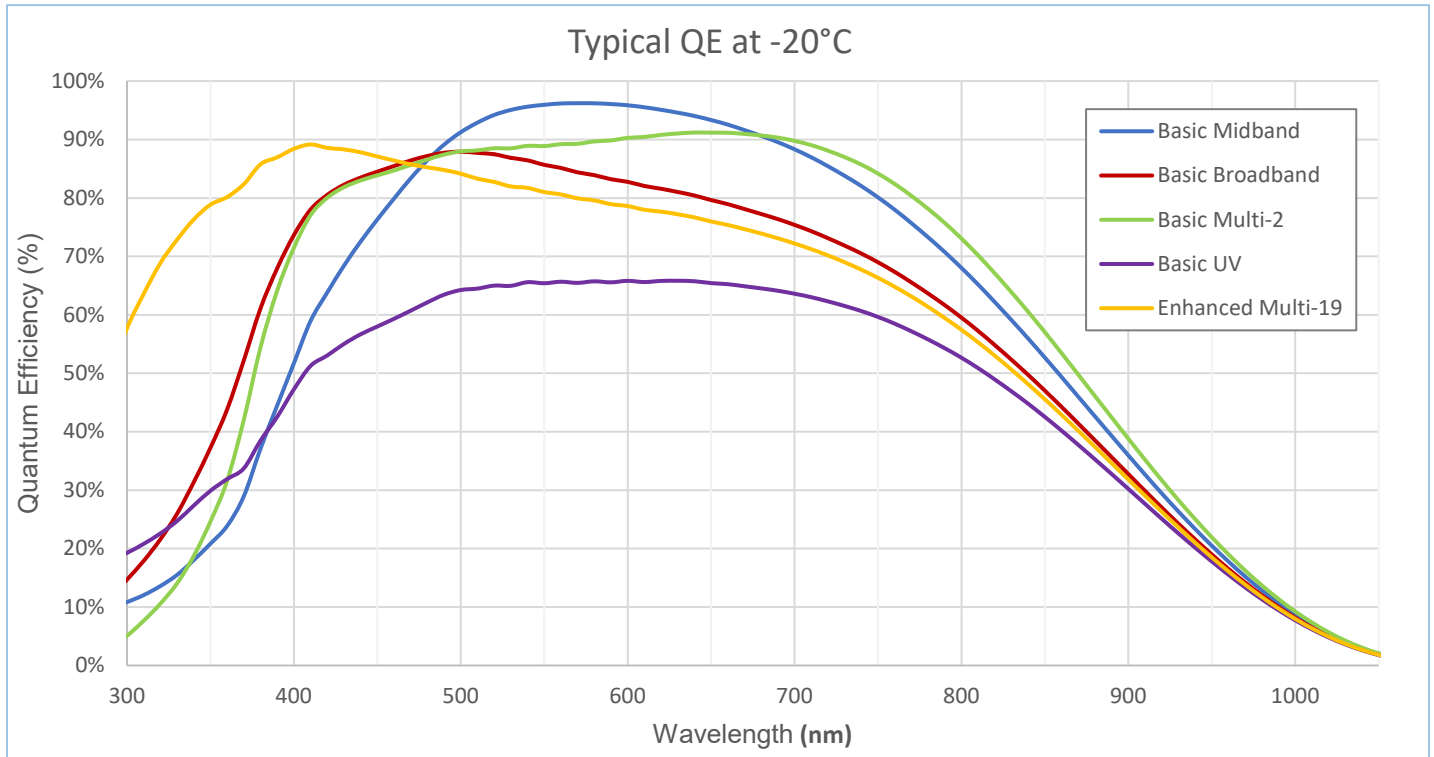
Except where otherwise specified, the following are measured at 18°C at a pixel rate of 11 MHz, with typical operating voltages. For the S28 variant, the parameters relating to the OSH amplifier do not apply; all other parameters are unchanged.

| Parameter | Min | Typical | Max | Units | Notes |
|--|-----|------------|------|------------------------------------|-------|
| Output amplifier responsivity, OSH amplifier | - | 5.3 | - | $\mu\text{V}/\text{e}^-$ | 2 |
| Output amplifier responsivity, OSL amplifier | - | 1.1 | - | $\mu\text{V}/\text{e}^-$ | 2, 3 |
| Multiplication register gain, OSL amplifier | 1 | - | 1000 | | 4 |
| Peak signal - 2-phase IMO | 90k | 150k | - | e^-/pixel | 5 |
| Charge handling capacity of multiplication register | - | 800k | - | e^-/pixel | 6 |
| Readout noise at 50 kHz with CDS, OSH amplifier | - | 2.2 | - | $\text{e}^- \text{ rms}$ | 7 |
| Readout noise at 1 MHz with CDS, OSH amplifier | - | 5.4 | - | $\text{e}^- \text{ rms}$ | 7 |
| Amplifier reset noise (without CDS), OSH amplifier | - | 50 | - | $\text{e}^- \text{ rms}$ | 7 |
| Readout noise at 50 kHz with CDS, OSL amplifier | - | 6 | - | $\text{e}^- \text{ rms}$ | 3, 7 |
| Readout noise at 15 MHz with CDS, OSL amplifier | - | 14 | - | $\text{e}^- \text{ rms}$ | 3, 7 |
| Amplifier reset noise (without CDS), OSL amplifier | - | 120 | - | $\text{e}^- \text{ rms}$ | 3, 7 |
| Readout noise at 1 MHz and 1000X gain | - | <1 | - | $\text{e}^- \text{ rms}$ | 7 |
| Maximum frequency (settling to 1%), OSH amplifier | - | - | 3 | MHz | 7, 8 |
| Maximum frequency (settling to 5%), OSH amplifier | - | - | 4.5 | MHz | 7, 8 |
| Maximum frequency (settling to 1%), OSL amplifier | - | - | 9 | MHz | 7, 8 |
| Maximum frequency (settling to 5%), OSL amplifier | - | - | 15 | MHz | 7, 8 |
| Maximum parallel transfer frequency | - | 1.6 | - | MHz | 2 |
| Dark signal equivalent at 20°C | - | 400 | 800 | $\text{e}^-/\text{pixel}/\text{s}$ | 9, 10 |
| Dark signal non-uniformity (DSNU) equivalent at 20°C | - | 60 | - | $\text{e}^-/\text{pixel}/\text{s}$ | 11 |
| Excess noise factor | - | $\sqrt{2}$ | - | | 12 |

NOTES

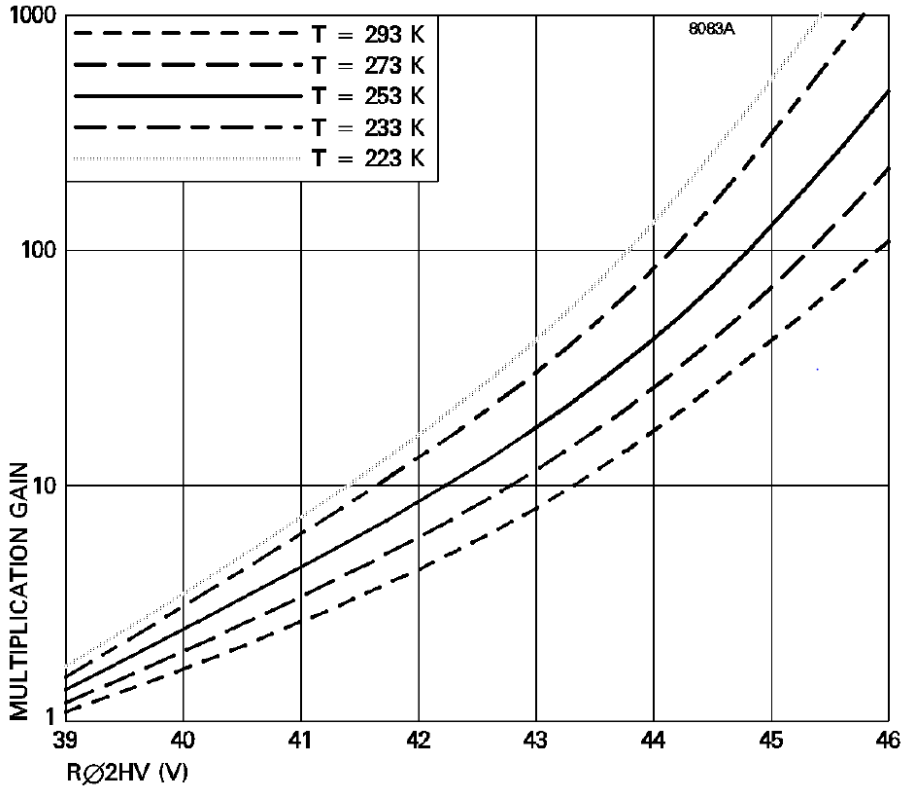
- For the Multi-19 variant a reduced format of 506 x 506 is recommended due to reduced responsivity at the edges of the image area.
- Measured at a pixel rate of 1 MHz.
- No EM gain applied.
- Some increase of R \emptyset 2HV may be required throughout life to maintain gain performance.
- For Multi-2 and Multi-19 variants, the peak signal is 95k e^- typical and 75k e^- min.
- When multiplicative gain is used, a linear response is achieved for output signals up to 400 ke $^-$.
- Values are inferred from design.
- The quoted maximum frequencies assume a 20 pF load and correlated double sampling (CDS) are being implemented. If instead a single sampling is used, the output will be settled to 1% at 15 MHz typically.
The quoted dark signal has the usual temperature dependence for inverted mode operation. For operation at high frame rates with short integration times, there will also be a significant component generated during readout through the non-inverted mode register.
- There exists a further weakly temperature dependant component, the clock induced charge (CIC), which is independent of integration time. For more information, refer to the technical note "Dark Signal and Clock-Induced Charge in L3Vision™ CCD Sensors".
- For fringe suppression variants, the dark signal will be higher (typical and maximum are 600 and 900 $\text{e}^-/\text{pixel}/\text{s}$ respectively).
- DSNU is defined as the 1 σ variation of the dark signal.
- The excess noise factor is defined as the factor by which the multiplication process increases the shot noise on the image when multiplication gain is used.

SPECTRAL RESPONSE



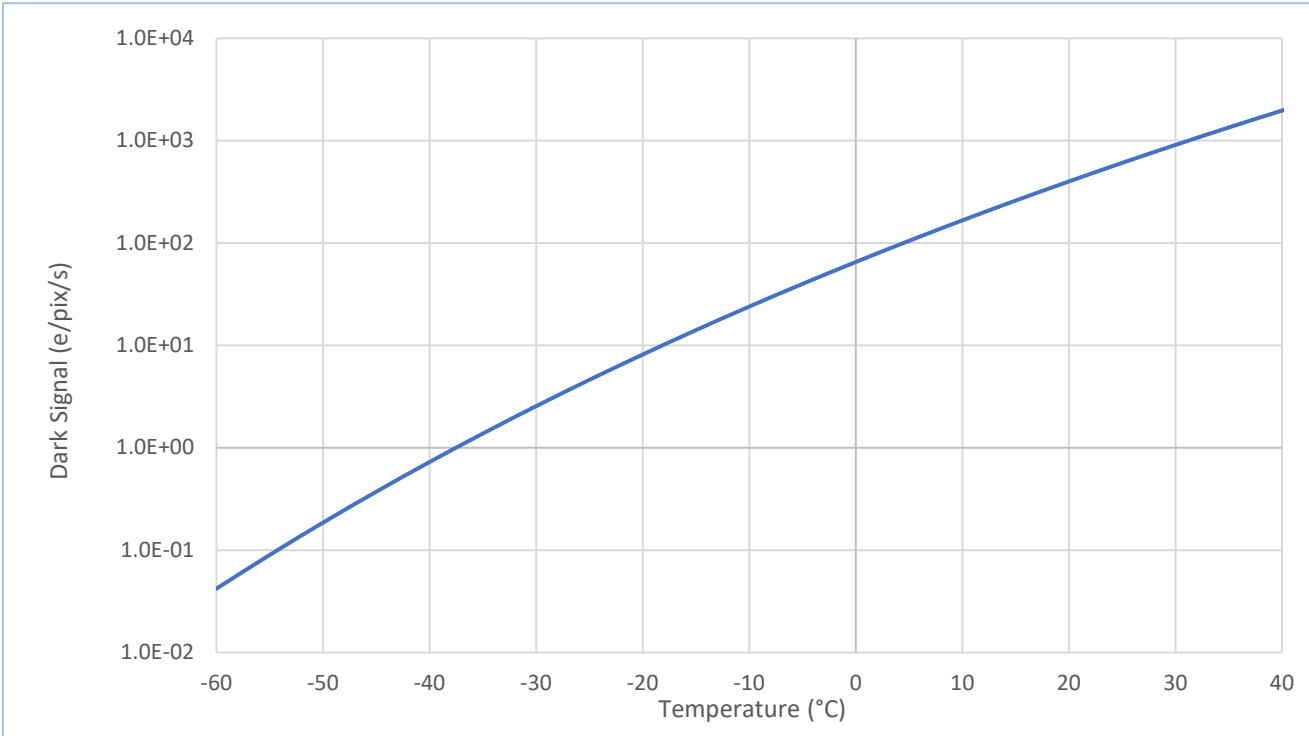
Devices can be supplied with alternative anti-reflection coatings optimised for different wavelengths – details from Teledyne e2v.

TYPICAL VARIATION OF MULTIPLICATIVE GAIN WITH RØ2HV MINUS RØDC



TYPICAL VARIATION OF DARK SIGNAL WITH TEMPERATURE

Dark signal is a strong function of temperature and the typical average (background) dark signal at any temperature T (kelvin) between 150 K and 300 K is given by $Q_d/Q_{do} = 1.14 \times 10^6 T^3 e^{-9080/T}$ where Q_{do} is the dark current at 293 K.



COSMETIC SPECIFICATION

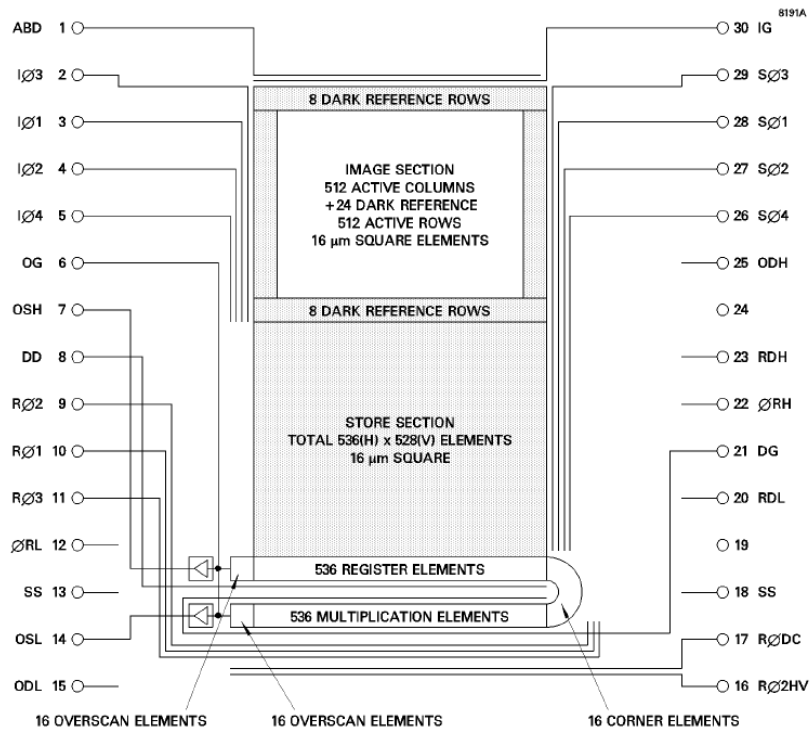
All cosmetic tests are performed at $18 \pm 3^\circ\text{C}$ in 2-phase inverted mode at 11MHz.

| Grade | 1 |
|------------------------|----|
| White Defects | 10 |
| White Columns | 0 |
| Black/Pin-head Columns | 0 |

Cosmetic definitions

| | |
|-------------------------------|---|
| White Defects | White defects are pixels having a dark signal generation rate corresponding to an output signal of greater than 5 times the maximum dark signal level. |
| White Columns | A white column contains at least 9 white defects. |
| Black/Pin-head Columns | <p>Black defects are counted when they have a responsivity of less than 80% of the local mean signal at approximately the specified gain and level of illumination. A black column contains at least 9 black defects.</p> <p>Pin-head columns are manifest as a partial dark column with a bright pixel showing photo-response at the end of the column nearest to the readout register. Pin-head columns are counted when the black column has a responsivity of less than 80% of the local mean signal at approximately the specified multiplication gain and level of illumination. A pin-head column contains at least 9 black defects.</p> |

DEVICE ARCHITECTURE



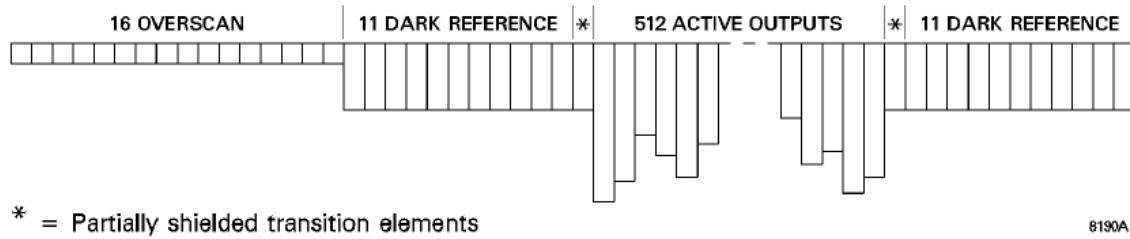
The rows and columns immediately adjacent to the active image area may be only partially shielded, i.e. transition elements, and should not be used for reference purposes.

The electrodes of the image and store sections are configured for four-phase clocking, but adjacent phases need to be joined off chip to run in two phase operation.

The multiplication register requires two extra drive phases, RØDC and RØ2HV.

There is a dump drain DD below the 536 register elements adjacent to the store section with the charge dumping operation controlled by the dump gate DG.

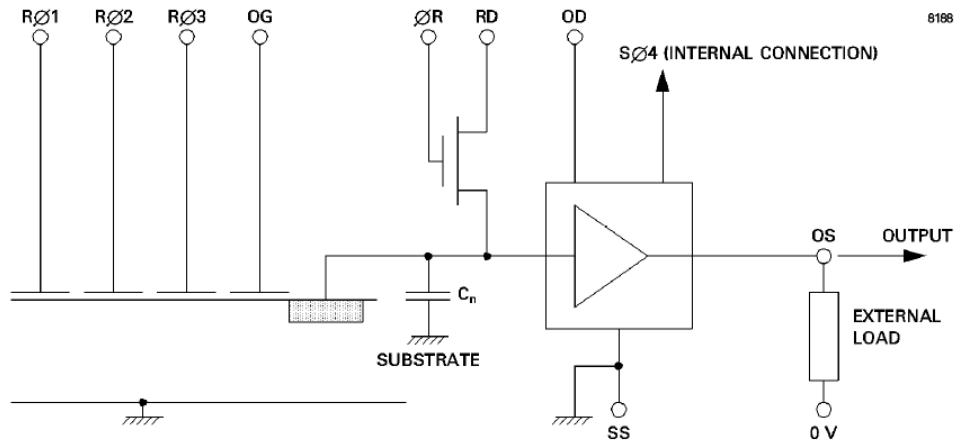
LINE OUTPUT FORMAT



NOTES

- there will be a one row propagation delay between transferring a row from the store section to the conventional register and then reading it out through the OSL CCD output.

OUTPUT CIRCUIT



The amplifiers have a DC restoration circuit that is internally activated whenever SØ4 is high.

Nominal Design Features (Not measured)

| Feature | OSH | OSL |
|---------------------|--------------|--------------|
| Output | OSH (pin 7) | OSL (pin 14) |
| External load | 5 kΩ or 5 mA | 5 kΩ or 5 mA |
| Output impedance | 250 Ω | 350 Ω |
| On-chip dissipation | 30 mW | 40 mW |

CONNECTIONS TYPICAL VOLTAGES AND ABSOLUTE MAXIMUM RATINGS

| Pin | Ref | Function | MIN (V) | MAX (V) |
|-----|---------------|-----------------------------|---------|---------|
| 1 | ABD | Anti-blooming drain | -0.3 | +25 |
| 2 | IØ3 | Image section clock phase 3 | -20 | +20 |
| 3 | IØ1 | Image section clock phase 1 | -20 | +20 |
| 4 | IØ2 | Image section clock phase 2 | -20 | +20 |
| 5 | IØ4 | Image section clock phase 4 | -20 | +20 |
| 6 | OG | Output gate | -20 | +20 |
| 7 | OSH (note 14) | Output source high | -0.3 | +25 |
| 8 | DD | Dump drain | -0.3 | +25 |
| 9 | RØ2 | Register clock phase 2 | -20 | +20 |
| 10 | RØ1 | Register clock phase 1 | -20 | +20 |
| 11 | RØ3 | Register clock phase 3 | -20 | +20 |
| 12 | ØRL | Output reset pulse low | -20 | +20 |
| 13 | SS | Substrate | 0 | |
| 14 | OSL | Output source low | -0.3 | +25 |
| 15 | ODL | Output drain low | -0.3 | +32 |
| 16 | RØ2HV | Register clock phase 2 HV | -20 | +50 |
| 17 | RØDC | Register DC phase | -20 | +20 |
| 18 | SS | Substrate | 0 | |
| 19 | n.c. | No connection | - | |
| 20 | RDL | Reset drain low | -0.3 | +25 |
| 21 | DG | Dump gate | -20 | +20 |
| 22 | ØR | Output reset pulse high | -20 | +20 |
| 23 | RDH | Reset drain high | -0.3 | +25 |
| 24 | n.c. | No connection | - | |
| 25 | ODH | Output drain high | -0.3 | +25 |
| 26 | SØ4 | Store section clock phase 4 | -20 | +20 |
| 27 | SØ2 | Store section clock phase 2 | -20 | +20 |
| 28 | SØ1 | Store section clock phase 1 | -20 | +20 |
| 29 | SØ3 | Store section clock phase 3 | -20 | +20 |
| 30 | IG | Isolation gate | -20 | +20 |

14. Pin 7 is n.c. no connection for S28 variant. The ABD pin is used for connection purposes and must be biased as specified even for non-anti-blooming variants.

MAXIMUM VOLTAGE BETWEEN PAIRS

| Pin | Ref | Pin | Ref | Min (V) | Max (V) |
|--------------------------------|-------|-----|------|---------|---------|
| 7 | OSH | 25 | ODH | -15 | +15 |
| 14 | OSL | 15 | ODL | -15 | +15 |
| 16 | RØ2HV | 17 | RØDC | -20 | +50 |
| 16 | RØ2HV | 11 | RØ3 | -20 | +50 |
| Output Transistor Current (mA) | | | | | 20 |

OPERATING VOLTAGES

Typical operating voltages are as given in the table below. Some adjustment within the minimum-maximum range specified may be required to optimise performance.

| Connection | Description | Phase Amplitude or DC level (V) | | | Notes |
|-------------------|---------------------------|---------------------------------|---------|-----|-------|
| | | Min | Typical | Max | |
| IØ1, 2, 3, 4 high | Image section: clock high | +5 | +7 | +9 | 15 |
| IØ1, 2, 3, 4 low | Image section: clock low | -6 | -5 | -4 | |
| SØ1, 2, 3, 4 high | Store section: clock high | +5 | +7 | +9 | 15 |
| SØ1, 2, 3, 4 low | Store section: clock low | -6 | -5 | -4 | |
| RØ1, 2, 3 high | Register: clock high | +8 | +12 | +13 | |
| RØ1, 2, 3 low | Register: clock low | - | 0 | - | |
| RØ2HV high | Register HV phase high | +20 | +40 | +50 | 5 |
| RØ2HV low | Register HV phase low | 0 | +4 | +5 | |
| ØR high | Reset clock high | - | +10 | - | 16 |
| ØR low | Reset clock low | - | 0 | - | |
| RØDC | Register DC phase | +2 | +3 | +5 | |
| OG | Output gate voltage | +1 | +3 | +5 | 17 |
| IG | Isolation gate voltage | - | -5 | - | |
| SS | Substrate | 0 | +4.5 | +7 | |
| ODL, ODH | Output drain | +25 | +28 | +32 | |
| RD | Reset drain voltage | +15 | +17 | +20 | |
| ABD | Anti-blooming Drain | +10 | +18 | +20 | |
| DG high | Dump gate high | - | 0 | - | |
| DG low | Dump gate low | +10 | +12 | +13 | |
| DD | Dump drain | +20 | +24 | +25 | |

NOTES

- IØ and SØ adjustment may be common. The high level may need to be adjusted to achieve correct charge transfer and the low level may need to be separately adjusted to achieve correct inverted mode operation that is uniform across the array. Alternatively, adjustment of SS with IØ and SØ low levels fixed at the nominal values can be used to achieve the same result.
- ØRL and ØRH high level may be adjusted in common with RØ1, 2, 3.
- Other than the output gates (OG), there are no common connections made between the two amplifiers, and either can be powered down by connecting the appropriate output drain (OD) connection to the substrate (SS). The reset drains (RD) should remain biased, with the reset gate (ØR) clocked normally or held at clock low level.

ELECTRICAL INTERFACE CHARACTERISTICS (not measured)

| ELECTRODE CAPACITANCES AT MID CLOCK LEVELS | | | | | SERIES RESISTANCES | |
|--|-------|-------------|-------|-------|--------------------|-------|
| Connection | To SS | Inter-phase | Total | Units | Total | Units |
| IØ1 | 3.7 | 1.6 | 5.3 | nF | 17 | Ω |
| IØ2 | 1.6 | 1.6 | 3.2 | nF | 17 | Ω |
| IØ3 | 3.7 | 1.6 | 5.3 | nF | 17 | Ω |
| IØ4 | 1.6 | 1.6 | 3.2 | nF | 17 | Ω |
| SØ1 | 3.7 | 1.6 | 5.3 | nF | 17 | Ω |
| SØ2 | 1.6 | 1.6 | 3.2 | nF | 17 | Ω |
| SØ3 | 3.7 | 1.6 | 5.3 | nF | 17 | Ω |
| SØ4 | 1.6 | 1.6 | 3.2 | nF | 17 | Ω |
| RØ1 | 50 | 65 | 115 | pF | 6 | Ω |
| RØ2 | 32 | 43 | 75 | pF | 6 | Ω |
| RØ3 | 62 | 63 | 125 | pF | 6 | Ω |
| RØ2HV | 28 | 37 | 65 | pF | 2 | Ω |

CLOCK TIMING REQUIREMENTS

The device is of a 4-phase construction, designed to operate in 2-phase inverted mode. This is achieved by applying common timings to phases Ø1 and Ø2, and phases Ø3 and Ø4 of the image and store sections. Suggested timing diagrams are shown in Figs. 4-11.

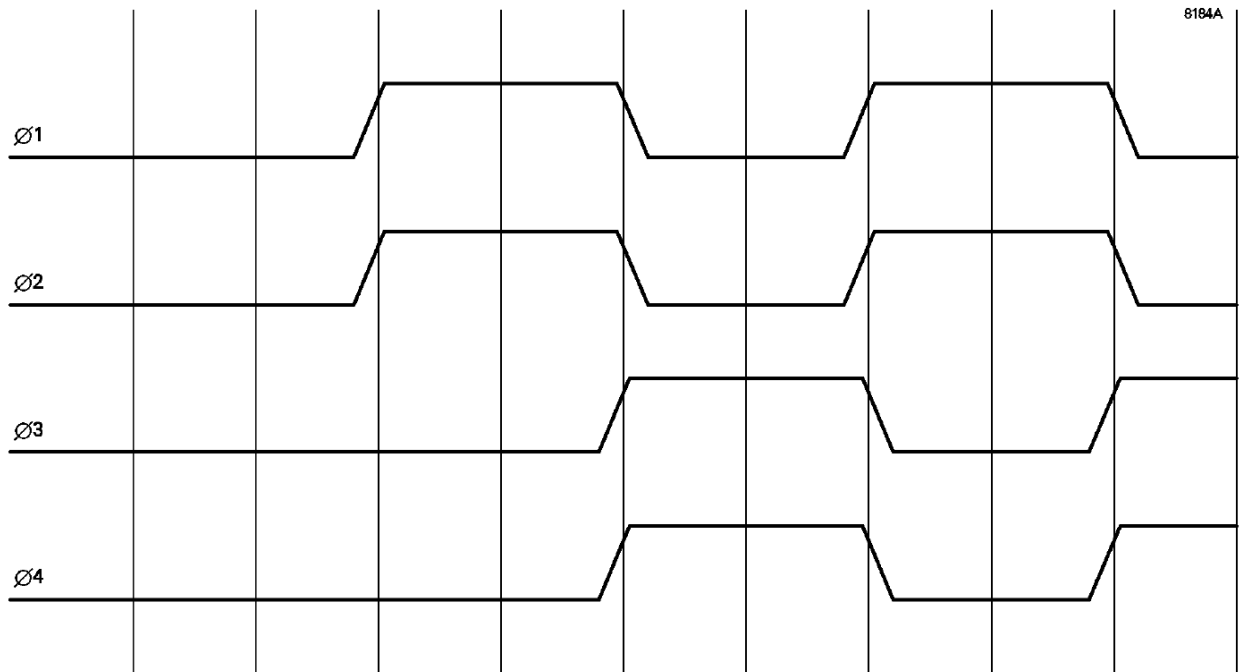
The following are suggested pulse rise and fall times:

| Clock Pulse | Typical Rise Time τ (ns) | Typical Fall Time τ (ns) | Typical Pulse Overlap |
|-------------|-------------------------------|-------------------------------|--|
| IØ | 120 < τ < 200 | 120 < τ < 200 | @90% points |
| SØ | 120 < τ < 200 | 120 < τ < 200 | @90% points |
| RØ1 | 10 | 10 | @70% points |
| RØ2 | 10 | 10 | @70% points |
| RØ3 | 10 | 10 | @70% points |
| RØ2HV | 25 | 25 | See 18 |
| RØ2HV | Sine | Sine | Sinusoid – high on falling edge of RØ1 |

NOTES

18. RØ2HV can be operated with a normal clock pulse, as shown in Fig. 6. Alternatively, a sinusoidal clocking scheme is shown in Fig. 5. The requirement for successful clocking is that RØ2HV reaches its maximum amplitude before RØ1 goes low.

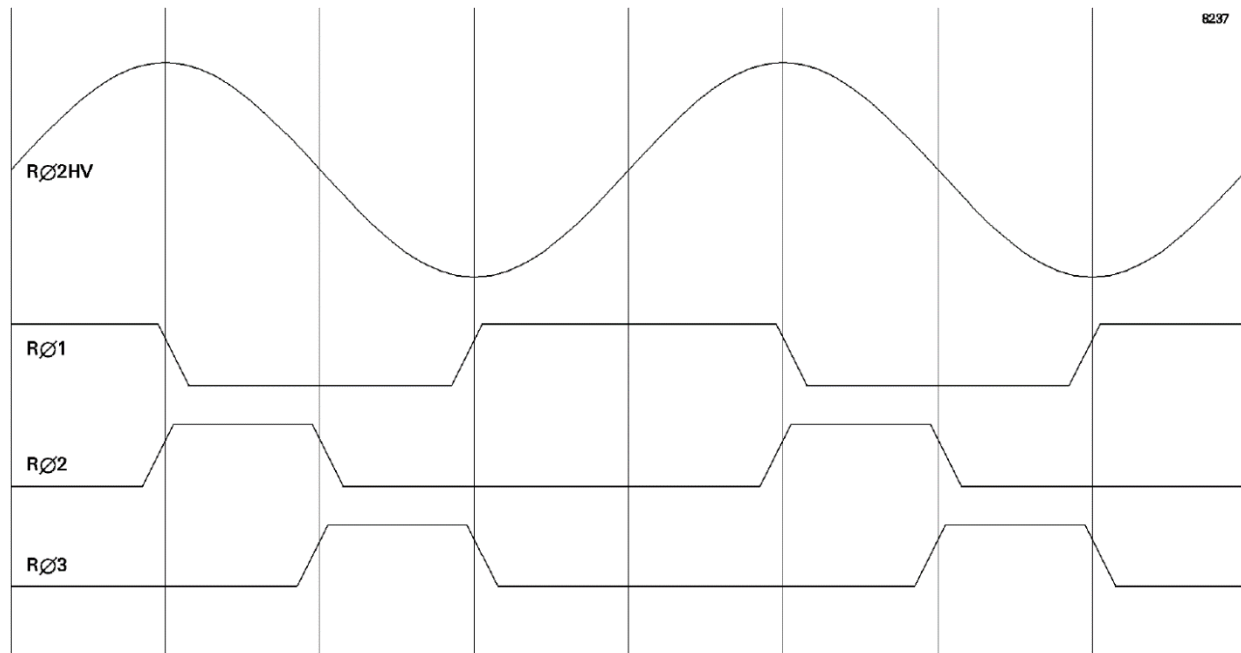
CLOCKING SCHEME FOR 2-PHASE INVERTED MODE OPERATION



CLOCKING SCHEME FOR MULTIPLICATION GAIN

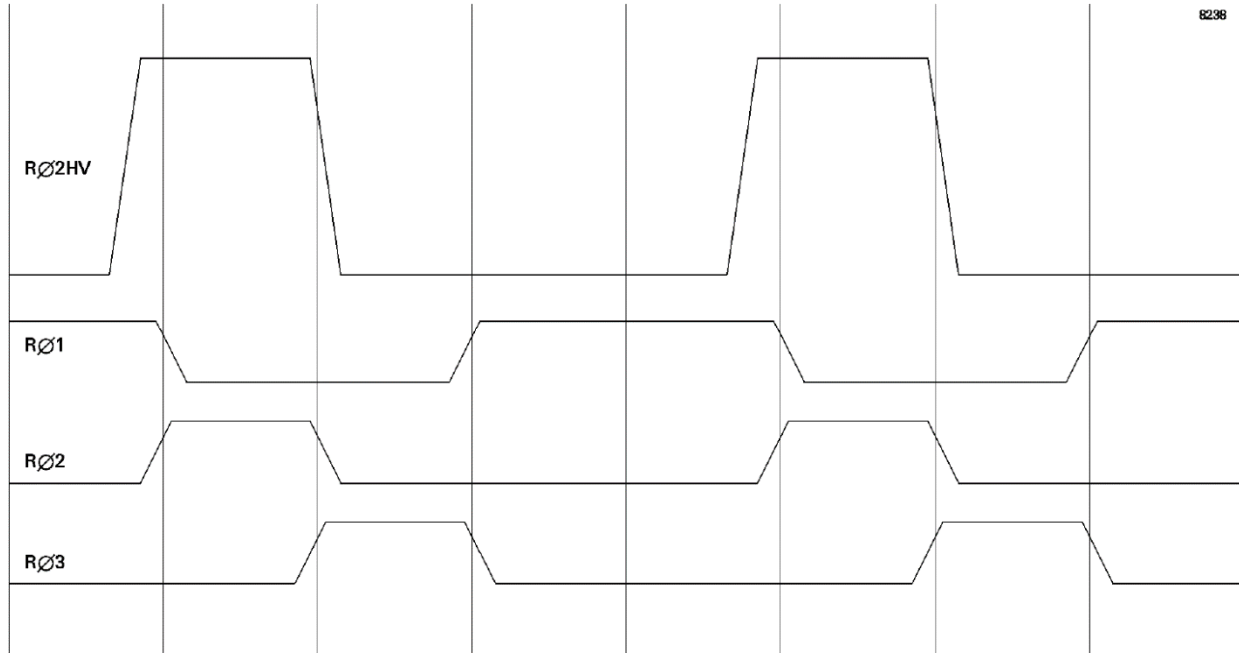
Sinusoidal Clcking Scheme

See note 19, used for factory testing



Trapezoidal Clocking Scheme

See note 19, not used in factory testing

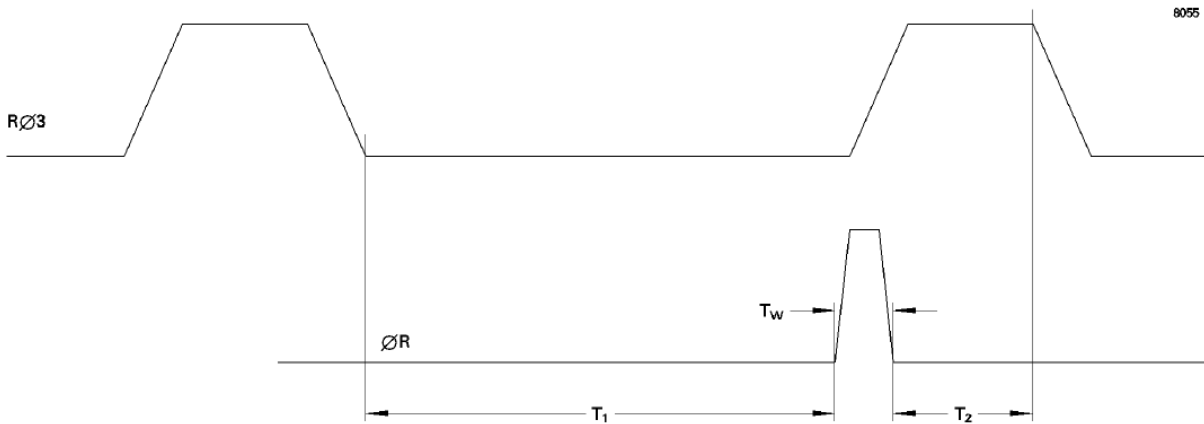


NOTES

19. To operate through the OSH output amplifier, the RØ1 and RØ2 waveforms should be interchanged.

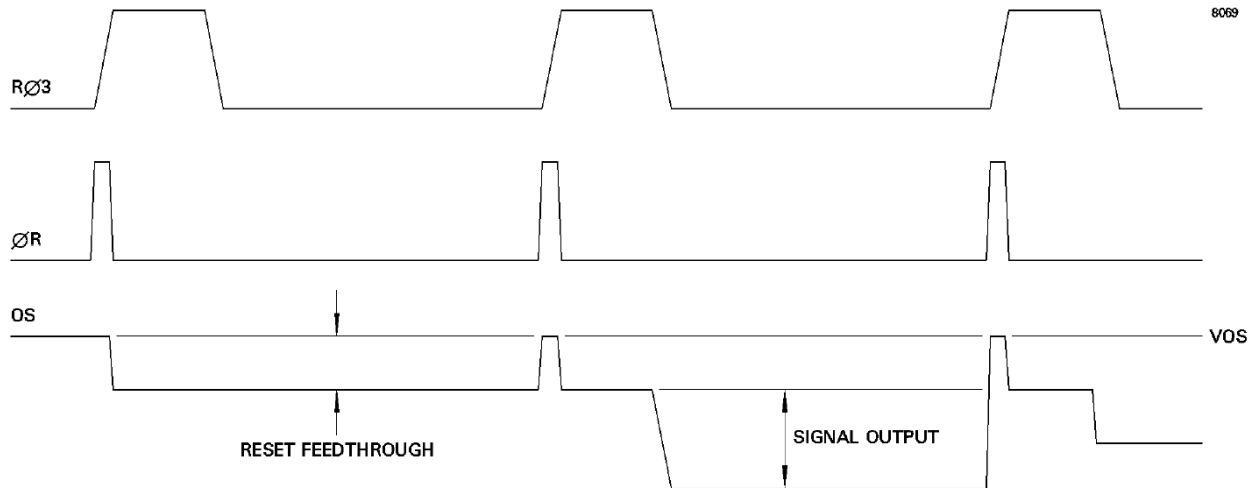
PULSE TIMINGS AND OVERLAPS

Reset Pulse

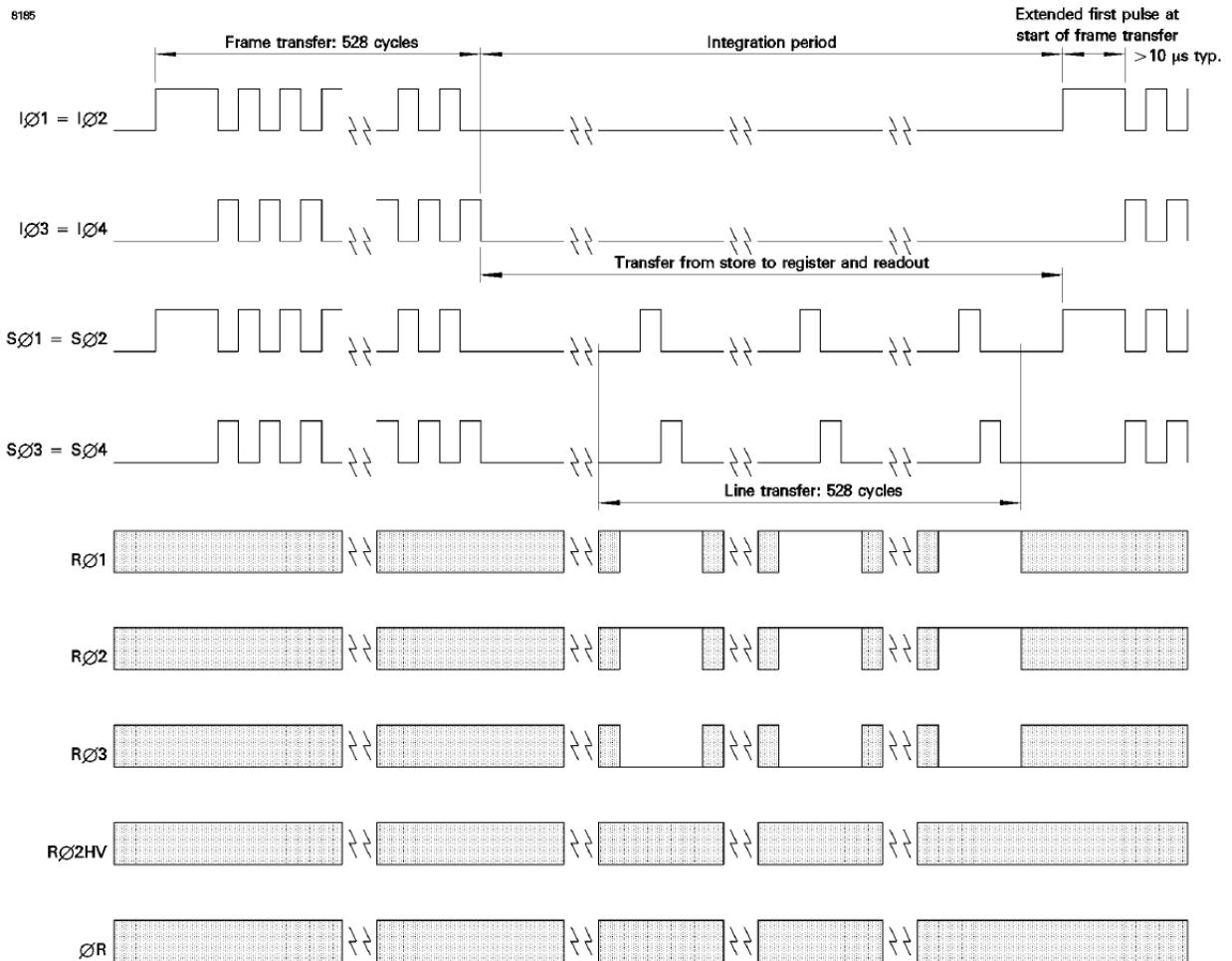


$T_w = 10 \text{ ns typical}$
 $T_1 = \text{output valid}$
 $T_2 > 0 \text{ ns}$

Pulse and Output Timing

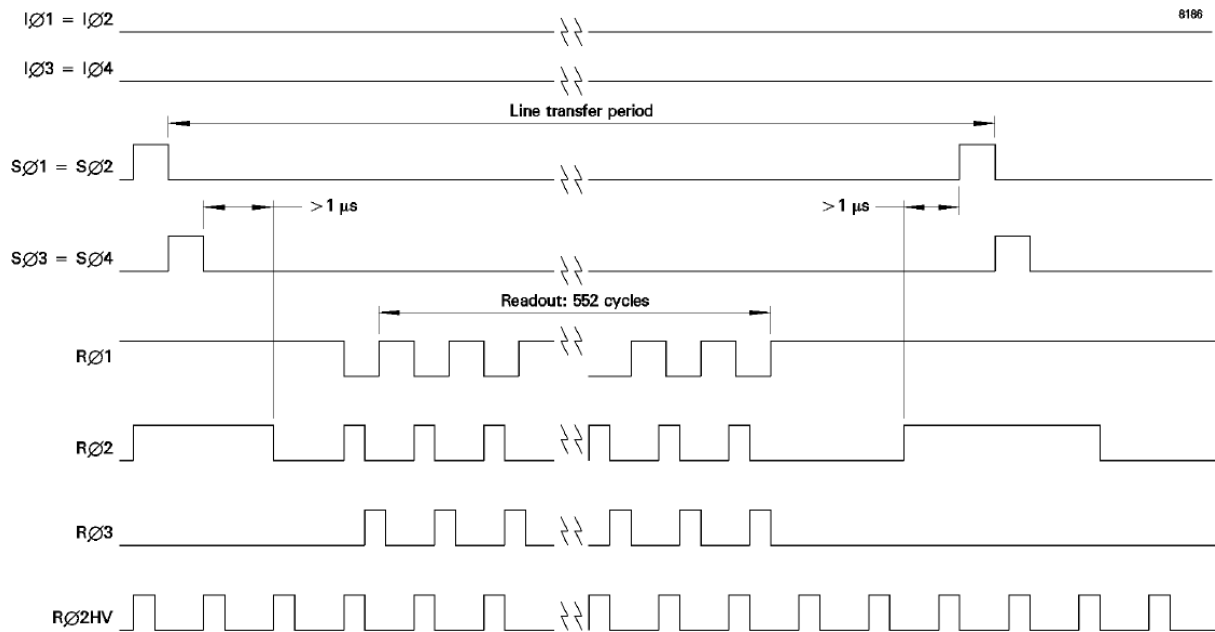


Example Frame Timing Diagram

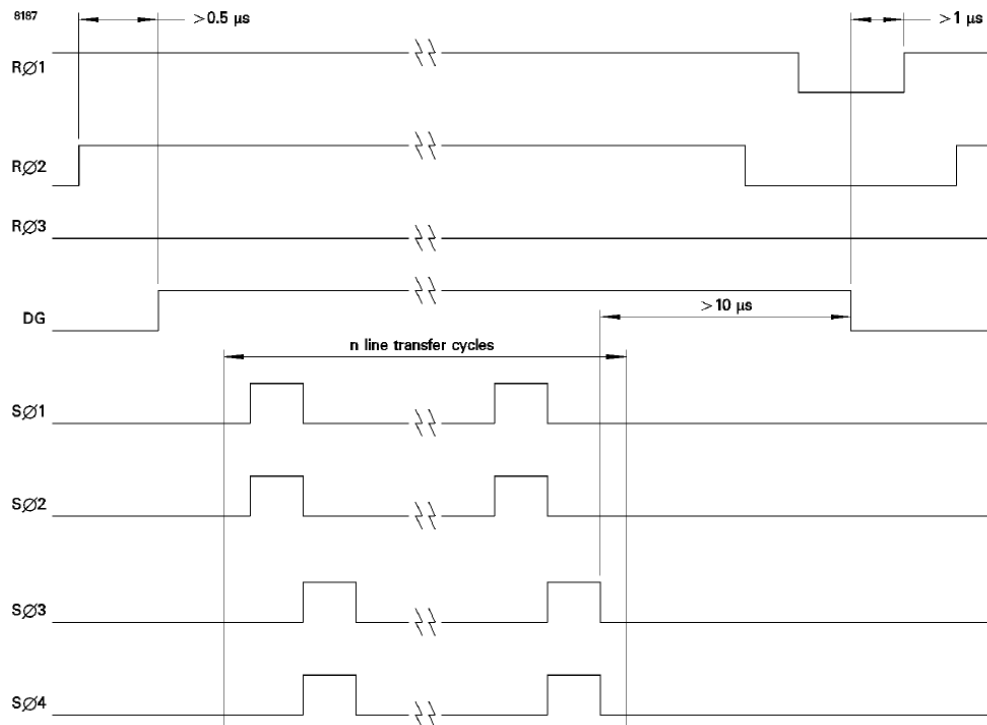


Example Line Timing Diagram

Operation through OSL, see notes 13 and 19



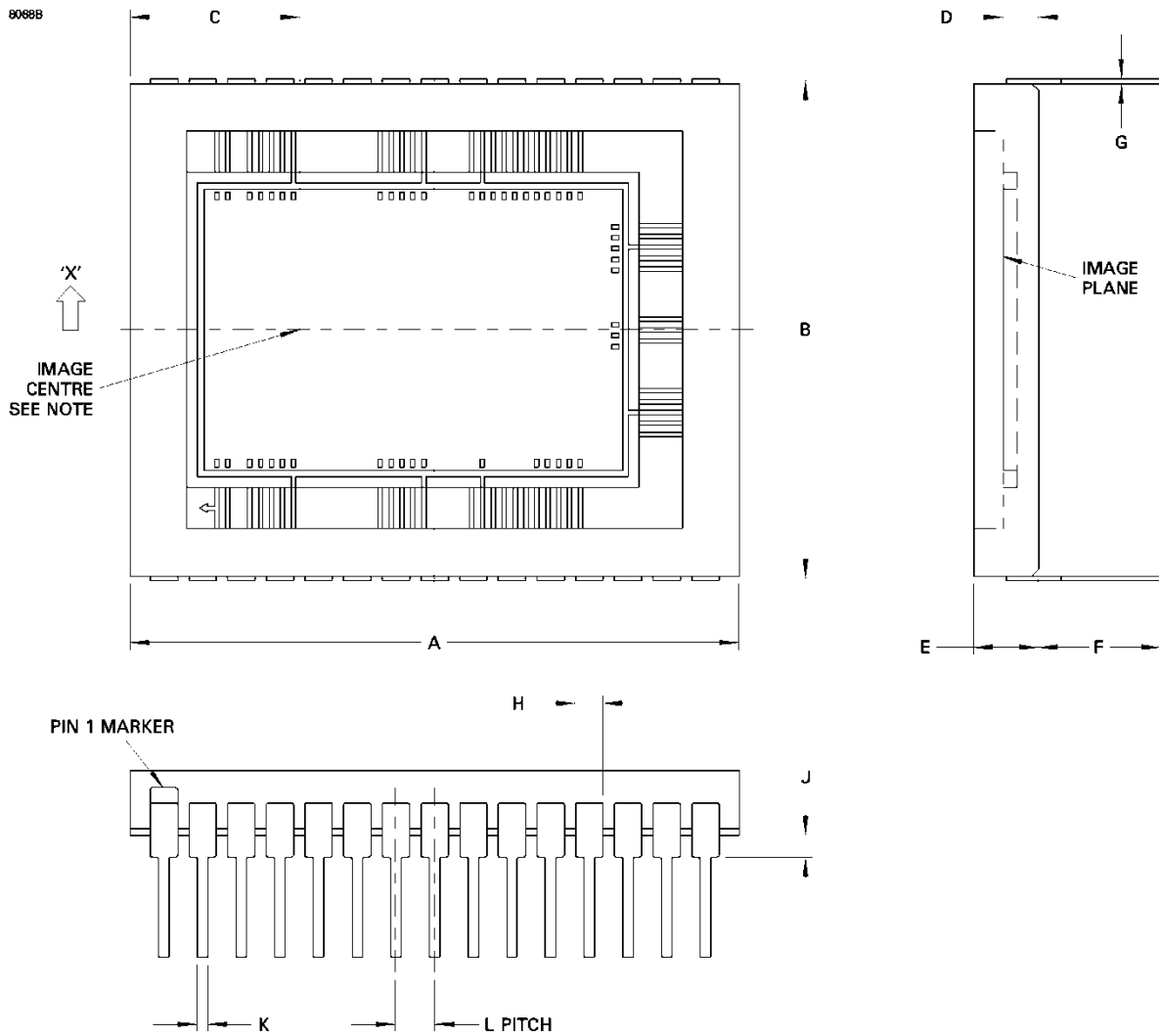
Operation of the Dump Gate to Dump n Lines of Unwanted Data From the Standard Register



Wanted lines of data must be completely read out before dumping unwanted data.

OUTLINE DRAWINGS

PACKAGE OUTLINE (Tolerances are by design and not verified on each part)



The image center is aligned centrally in the package in direction 'X', to within a tolerance of $\pm 0.20\text{mm}$.

HEALTH AND SAFETY HAZARDS

Teledyne e2v devices are safe to handle and operate, provided that the relevant precautions stated herein are observed. Teledyne e2v does not accept responsibility for damage or injury resulting from the use of devices it produces. Equipment manufacturers and users must ensure that adequate precautions are taken. Appropriate warning labels and notices must be provided on equipment incorporating Teledyne e2v devices and in operating manuals.

HANDLING CCD SENSORS

CCD sensors, in common with most high performance MOS IC devices, are static sensitive. In certain cases a discharge of static electricity may destroy or irreversibly degrade the device. Accordingly, full anti-static handling precautions should be taken whenever using a CCD sensor or module. These include:

- Working at a fully grounded workbench
- Operator wearing a grounded wrist strap
- All receiving socket pins to be positively grounded
- Unattended CCDs should not be left out of their conducting foam or socket.

Evidence of incorrect handling will invalidate the warranty.

HIGH ENERGY RADIATION

Device parameters may begin to change if subject to an ionising radiation. Users planning to use CCDs in a high radiation environment are advised to contact Teledyne e2v.

TEMPERATURE LIMITS

| | Min | Typical | Max |
|-----------------|------------|----------------|------------|
| Storage | -200°C | | +100°C |
| Operating | -120°C | | +75°C |

Operation or storage in humid conditions may give rise to ice on the sensor surface on cooling, causing irreversible damage.

Maximum device heating/cooling..... 5 K/min

PART REFERENCES

| Variant | Operating Mode | Illumination | Enhanced BSI Process | Silicon | AR Coating | Fringe Suppression | Notes |
|----------------|----------------|--------------|----------------------|----------|------------|--------------------|-------|
| CCD97-00-G-095 | 2-Phase | BSI | No | Standard | Midband | No | |
| CCD97-00-G-103 | 2-Phase | BSI | No | Standard | Midband | No | 20 |
| CCD97-00-G-162 | 2-Phase | BSI | No | Standard | Broadband | No | |
| CCD97-00-G-172 | 2-Phase | BSI | No | Standard | Midband | Yes | |
| CCD97-00-G-175 | 2-Phase | BSI | No | Standard | Multi-2 | No | |
| CCD97-00-G-177 | 2-Phase | BSI | No | Standard | UV | No | |
| CCD97-00-G-180 | 2-Phase | BSI | No | Standard | Multi-2 | Yes | |
| CCD97-00-G-S28 | 2-Phase | BSI | No | Standard | Midband | No | 21 |
| CCD97-00-G-S74 | 2-Phase | BSI | Yes | Standard | Multi-19 | No | |

Grade Definitions

| | | |
|----------------|-------------------|--|
| Grade 1 | Science Grade | Meets all performance parameters and Grade 1 cosmetic parameters |
| Grade 5 | Engineering Grade | Electrically functional with no performance or cosmetic parameter guarantees |
| Grade 6 | Mechanical Grade | Non-functional. Mechanically representative only. |

NOTES

20. Lumogen coated device.
21. OSH output capability not included.
22. G = Grade (e.g. 1)
23. Additional variants may be available to custom order. Consult Teledyne e2v for more information.